

IRFP1405PBF

Data Sheet

Single N-Channel 55 V 310 W 120 nC Hexfet Power Mosfet Flange Mount - TO-247AC

Manufacturers	Infineon Technologies Corporation	J
Package/Case	TO-247AC	
Product Type	Transistors	
RoHS	Green	Images are for reference only
Lifecycle		

Please submit RFQ for IRFP1405PBF or Email to us: sales@ovaga.com We will contact you in 12 hours.

<u>RFQ</u>

General Description

Specifically designed for Automotive applications, this HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this design are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications.

Features

Planar cell structure for wide SOA

Optimized for broadest availability from distribution partners

Product qualification according to JEDEC standard

Silicon optimized for applications switching below <100kHz

Industry standard through-hole power package

High-current carrying capability package (up to 195 A, die-size dependent)

Targeted for high power density



Related Products



IRLTS6342TRPBF

Infineon Technologies Corporation TSOP-6



<u>IRF9310PBF</u>

Infineon Technologies Corporation SOIC-8



IRF9358TRPBF Infineon Technologies Corporation SOP-8



IRFB3307ZPBF Infineon Technologies Corporation TO-220AB









IRLHS6376TRPBF

Infineon Technologies Corporation PQFN2x2DD

IRFH9310TRPBF

Infineon Technologies Corporation PQFN-8

IRFB7430PBF

Infineon Technologies Corporation TO-220

IRF7351TRPBF

Infineon Technologies Corporation SOIC-8